

Power Matters.™

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>			1.00	V
DC Current Gain	HFE	25.00		100.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			100.00	V
Collector Current (dc)	I <sub>C</sub>			50.00	A
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>			100.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			7.00	V
Power Dissipation, Total	P <sub>T</sub>			125.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ PNP Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ PNP Transistor

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